

Charge disproportionation in organic conductors

Koichi Ichimura^{1*}, Kazuhiro Katono¹, Tomoya Taniguchi¹, Yuki Kawashima¹,
Satoshi Tanda¹, Kaoru Yamamoto²

¹Department of Applied Physics, Hokkaido University, Sapporo 060-8628, Japan

²Department of Applied Physics, Okayama University of Science, Okayama 700-0005, Japan

The electronic state of two dimensional organic conductors α -(BEDT-TTF)₂X was studied by scanning tunneling microscopy (STM). The conducting plane of single crystals was investigated at room temperature.

Figure 1 shows STM current image of α -(BEDT-TTF)₂I₃, which undergoes the charge ordering state below T_{CO} =135 K due to the long range Coulomb interaction. BEDT-TTF donor molecules were clearly imaged as bright spots. The obtained donor arrangement is characterized as α -type arrangement, in which there are two donor stacks in the unit cell. We found that the brightness of spots varies alternatively along the a -axis. Such a modulation cannot be expected from the crystal structure. It suggests the charge disproportionation which forms charge stripe structure even above T_{CO} [1].

We also investigated other materials with similar donor arrangement. Figure 2 shows current image of α -(BEDT-TTF)₂KHg(SCN)₄ (K-salt) at room temperature. The material undergoes the density wave state below T_{DW} =8 K. The donor arrangement is also recognized clearly as α -type. We found charge stripe modulation even in this salt, which does not undergoes the charge ordering state. Furthermore, we studied α -(BEDT-TTF)₂RbHg(SCN)₄ (Rb-salt). The salt is isomorphic with K-salt and its ground state is the density wave state with T_{DW} =12 K. The charge stripe structure was also found in Rb-salt.

The charge stripe structure was found in three different salts with the same donor arrangement at much higher temperature than their transition temperature. We think that the charge disproportionation at room temperature is common feature in α -(BEDT-TTF)₂X.

*Email: ichimura@eng.hokudai.ac.jp

References

[1] K. Katono, T. Taniguchi, K. Ichimura, Y. Kawashima, S. Tanda and K. Yamamoto, *Phys. Rev. B*, **91**, 125110 (2015).

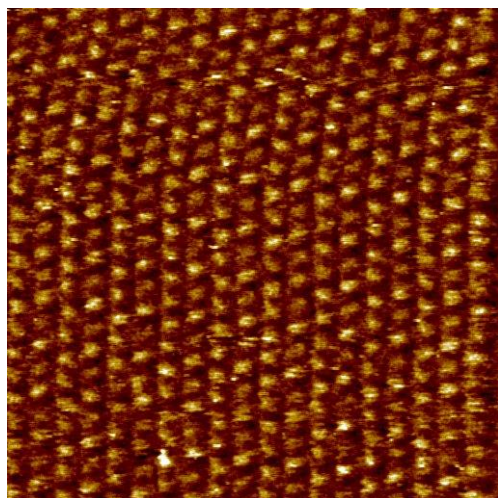


Fig. 1. STM image of the conducting plane of α -(BEDT-TTF)₂I₃ at 290 K. Scan area is 9.4×9.4 nm².

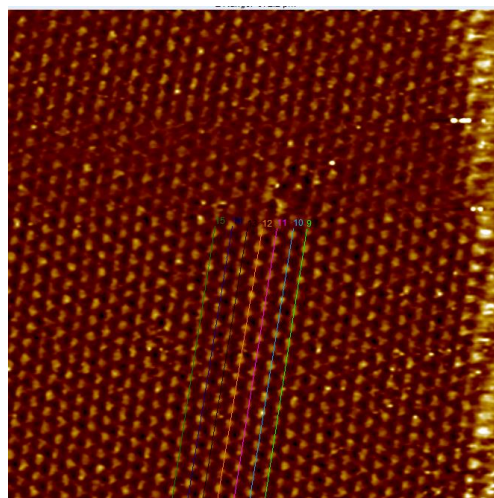


Fig. 2. STM image of the conducting plane of α -(BEDT-TTF)₂KHg(SCN)₄ at 290 K. Scan area is 15×15 nm².